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Vishay Siliconix

# Automotive P-Channel 40 V (D-S) 175 °C MOSFET

# PowerPAK® 1212-8W Single D D D B T Top View Bottom View

Marking code: Q036

PRODUCT SUMMARY	
V <sub>DS</sub> (V)	-40
$R_{DS(on)}(\Omega)$ at $V_{GS} = -10 \text{ V}$	0.0161
$R_{DS(on)}$ ( $\Omega$ ) at $V_{GS} = -4.5 \text{ V}$	0.0230
I <sub>D</sub> (A)	-16
Configuration	Single
Package	PowerPAK 1212-8W

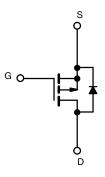
#### **FEATURES**

- TrenchFET® power MOSFET
- AEC-Q101 qualified <sup>d</sup>
- 100 % Rq and UIS tested
- Material categorization: for definitions of compliance please see www.vishav.com/doc?99912





ROHS COMPLIANT HALOGEN FREE



P-Channel MOSFET

ABSOLUTE MAXIMUM RATING	<b>GS</b> (T <sub>C</sub> = 25 °C, unles	ss otherwise noted)		
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V <sub>DS</sub>	-40	V
Gate-source voltage		$V_{GS}$	± 20	V
Continuous drain current a	T <sub>C</sub> = 25 °C	1	-16	
Continuous drain current -	T <sub>C</sub> = 125 °C	l <sub>D</sub>	-16	
Continuous source current (diode conduction) <sup>a</sup>		I <sub>S</sub>	-16	Α
Pulsed drain current <sup>b</sup>		I <sub>DM</sub>	-64	
Single pulse avalanche current	L = 0.1 mH	I <sub>AS</sub>	-25	
Single pulse avalanche energy	L=0.11IIII	E <sub>AS</sub>	31.2	mJ
Maximum power dissipation <sup>b</sup>	T <sub>C</sub> = 25 °C	Ъ	62.5	W
waximum power dissipation ~	T <sub>C</sub> = 125 °C	P <sub>D</sub>	20	VV
Operating junction and storage temperature range		T <sub>J</sub> , T <sub>stg</sub>	-55 to +175	°C
Soldering recommendations (peak temperature) e, f			260	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount <sup>c</sup>	R <sub>thJA</sub>	81	°C/W
Junction-to-case (drain)		$R_{thJC}$	2.4	C/VV

#### Notes

- a. Package limited
- b. Pulse test; pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. Parametric verification ongoing
- e. See solder profile (<a href="https://www.vishay.com/doc?73257">www.vishay.com/doc?73257</a>). The PowerPAK 1212-8W is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- f. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components



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PARAMETER	SYMBOL	TES	T CONDITIONS	MIN.	TYP.	MAX.	UNIT	
Static		^					ı	
Drain-source breakdown voltage	V <sub>DS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-40	-	-	.,	
Gate-source threshold voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =	V <sub>GS</sub> , I <sub>D</sub> = -250 μA	-1.5	-2.0	-2.5	V	
Gate-source leakage	I <sub>GSS</sub>	V <sub>DS</sub> =	0 V, V <sub>GS</sub> = ± 20 V	-	-	± 100	nA	
		$V_{GS} = 0 V$	V <sub>DS</sub> = -40 V	-	-	-1		
Zero gate voltage drain current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 125 °C	-	-	-50	μΑ	
		V <sub>GS</sub> = 0 V	V <sub>DS</sub> = -40 V, T <sub>J</sub> = 175 °C	-	-	-150		
On-state drain current a	I <sub>D(on)</sub>	V <sub>GS</sub> = -10 V	$V_{DS} \le -5 \text{ V}$	-20	-	-	Α	
		V <sub>GS</sub> = -10 V	I <sub>D</sub> = -12 A	-	0.0130	0.0161		
Drain aguras en atata registanas h	Ь	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -12 A, T <sub>J</sub> = 125 °C	-	-	0.0240	00 nA 1 10 μA 50 A 161 240 270 230 S 25 5 pF 97 22 nC .5 5 Ω .3 7 ns	
Drain-source on-state resistance b	R <sub>DS(on)</sub>	V <sub>GS</sub> = -10 V	I <sub>D</sub> = -12 A, T <sub>J</sub> = 175 °C	-	-	0.0270		22
		V <sub>GS</sub> = -4.5 V	I <sub>D</sub> = -9 A	-	0.0177	0.0230		
Forward transconductance b	9 <sub>fs</sub>	V <sub>DS</sub> :	= -15 V, I <sub>D</sub> = -7 A	-	30	-	S	
Dynamic <sup>b</sup>								
Input capacitance	C <sub>iss</sub>			-	3710	4825		
Output capacitance	C <sub>oss</sub>	$V_{GS} = 0 V$	$V_{DS} = -25 \text{ V}, f = 1 \text{ MHz}$	-	242	315	рF	
Reverse transfer capacitance	C <sub>rss</sub>			-	228	297		
Total gate charge <sup>c</sup>	Qg			-	63	82		
Gate-source charge <sup>c</sup>	Q <sub>gs</sub>	$V_{GS} = -10 \text{ V}$	$V_{DS} = -20 \text{ V}, I_{D} = -2.5 \text{ A}$	1	9	12	nC	
Gate-drain charge <sup>c</sup>	$Q_{gd}$			-	12	15.5		
Gate resistance	$R_g$	f = 1 MHz		2.8	4.6	7.5	Ω	
Turn-on delay time <sup>c</sup>	t <sub>d(on)</sub>			-	11.8	15.3		
Rise time <sup>c</sup>	t <sub>r</sub>	V <sub>DD</sub> :	$V_{DD}$ = -20 V, $R_L$ = 8 $\Omega$		3.6	4.7	200	
Turn-off delay time <sup>c</sup>	t <sub>d(off)</sub>	I <sub>D</sub> ≅ -2.5 A,	$V_{GEN}$ = -10 V, $R_g$ = 1 $\Omega$	ı	64	83	IIS	
Fall time <sup>c</sup>	t <sub>f</sub>	]		1	16	21.2	<u> </u>	
Source-Drain Diode Ratings and Char	acteristics <sup>b</sup>							
Pulsed current <sup>a</sup>	I <sub>SM</sub>			1	-	-64	Α	
Forward voltage	$V_{SD}$	1	-8.8 A, V <sub>GS</sub> = 0 V	_	-0.8	-1.2	V	

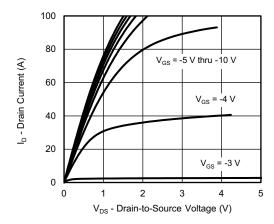
#### Notes

- a. Pulse test; pulse width  $\leq 300~\mu\text{s},$  duty cycle  $\leq 2~\%$
- b. Guaranteed by design, not subject to production testing
- c. Independent of operating temperature

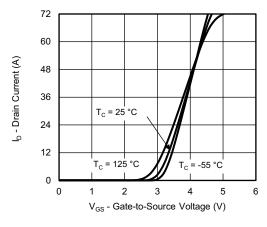
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



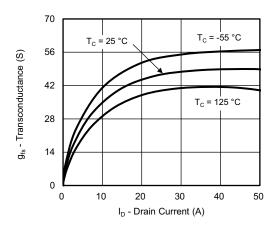
## **TYPICAL CHARACTERISTICS** (T<sub>A</sub> = 25 °C, unless otherwise noted)



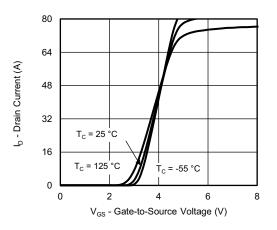
#### **Output Characteristics**



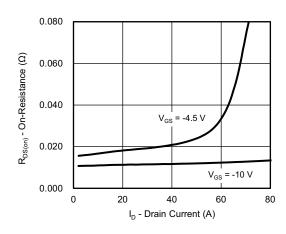
### Transfer Characteristics



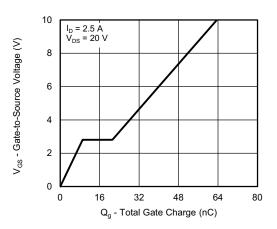
Transconductance



#### **Transfer Characteristics**



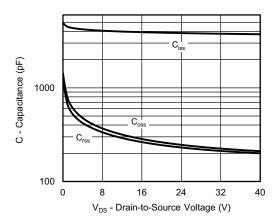
#### **On-Resistance vs. Drain Current**



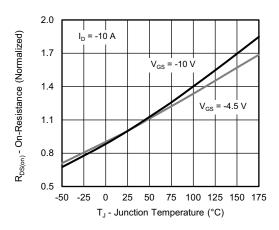
Capacitance



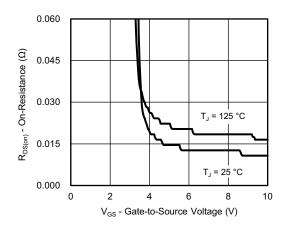
## TYPICAL CHARACTERISTICS (T<sub>A</sub> = 25 °C, unless otherwise noted)



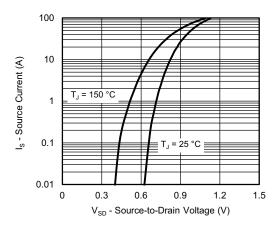
#### Capacitance



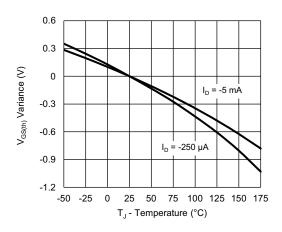
On-Resistance vs. Junction Temperature



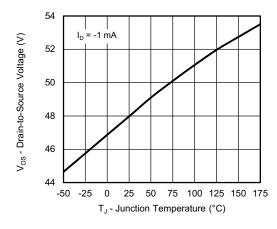
On-Resistance vs. Gate-to-Source Voltage



#### **Source Drain Diode Forward Voltage**



#### **Threshold Voltage**

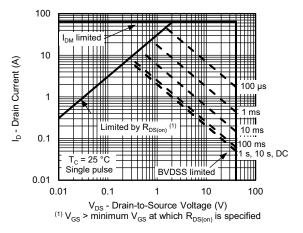


**Drain Source Breakdown vs. Junction Temperature** 

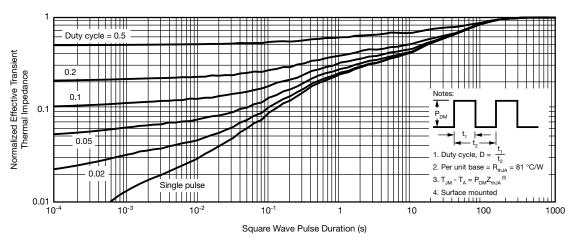
For technical questions, contact: automostechsu



# **THERMAL RATINGS** ( $T_A = 25$ °C, unless otherwise noted)



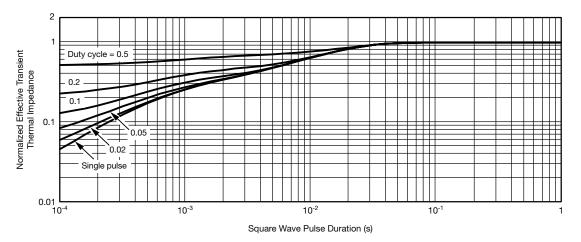
Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Ambient



## THERMAL RATINGS (T<sub>A</sub> = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Case

#### Note

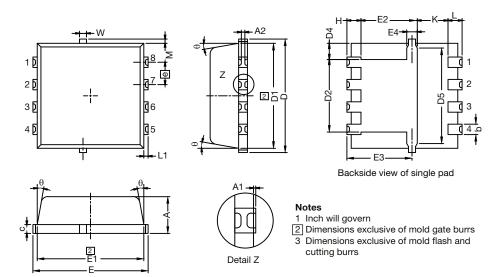
- The characteristics shown in the two graphs
  - Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
  - Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

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# PowerPAK® 1212-8W Case Outline



DIM		MILLIMETERS			INCHES	
DIM.	MIN.	NOM.	MAX.	MIN.	NOM.	MAX.
Α	0.97	1.04	1.12	0.038	0.041	0.044
A1	0	=	0.05	0	-	0.002
A2	0	-	0.13	0	-	0.005
b	0.23	0.30	0.41	0.009	0.012	0.016
С	0.23	0.28	0.33	0.009	0.011	0.013
D	3.20	3.30	3.40	0.126	0.130	0.134
D1	2.95	3.05	3.15	0.116	0.120	0.124
D2	1.98	2.11	2.24	0.078	0.083	0.088
D4	0.47 typ.			0.0185 typ.		
D5	2.3 typ.			0.090 typ.		
Е	3.20	3.30	3.40	0.126	0.130	0.134
E1	2.95	3.05	3.15	0.116	0.120	0.124
E2	1.47	1.60	1.73	0.058	0.063	0.068
E3	1.75	1.85	1.98	0.069	0.073	0.078
E4	0.34 typ.			0.013 typ.		
е	0.65 BSC.		0.026 BSC			
K	0.86 typ.			0.034 typ.		
Н	0.30	0.41	0.51	0.012	0.016	0.020
L	0.30	0.43	0.56	0.012	0.017	0.022
L1	0.06	0.13	0.20	0.002	0.005	0.008
θ	0°	-	12°	0°	-	12°
W	0.15	0.25	0.36	0.006	0.010	0.014
М	0.125 typ.				0.005 typ.	

DWG: 6032



# RECOMMENDED MINIMUM PADS FOR PowerPAK® 1212-8 Single



Recommended Minimum Pads Dimensions in Inches/(mm)

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APPLICATION NOTE



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